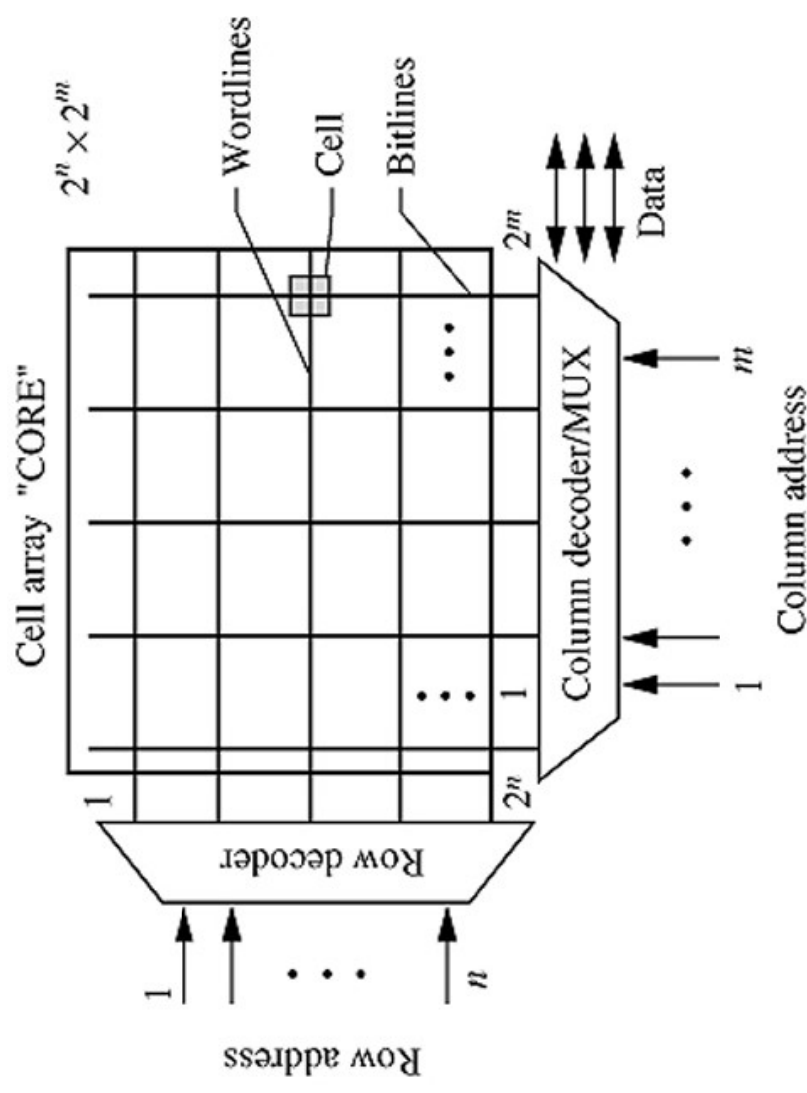


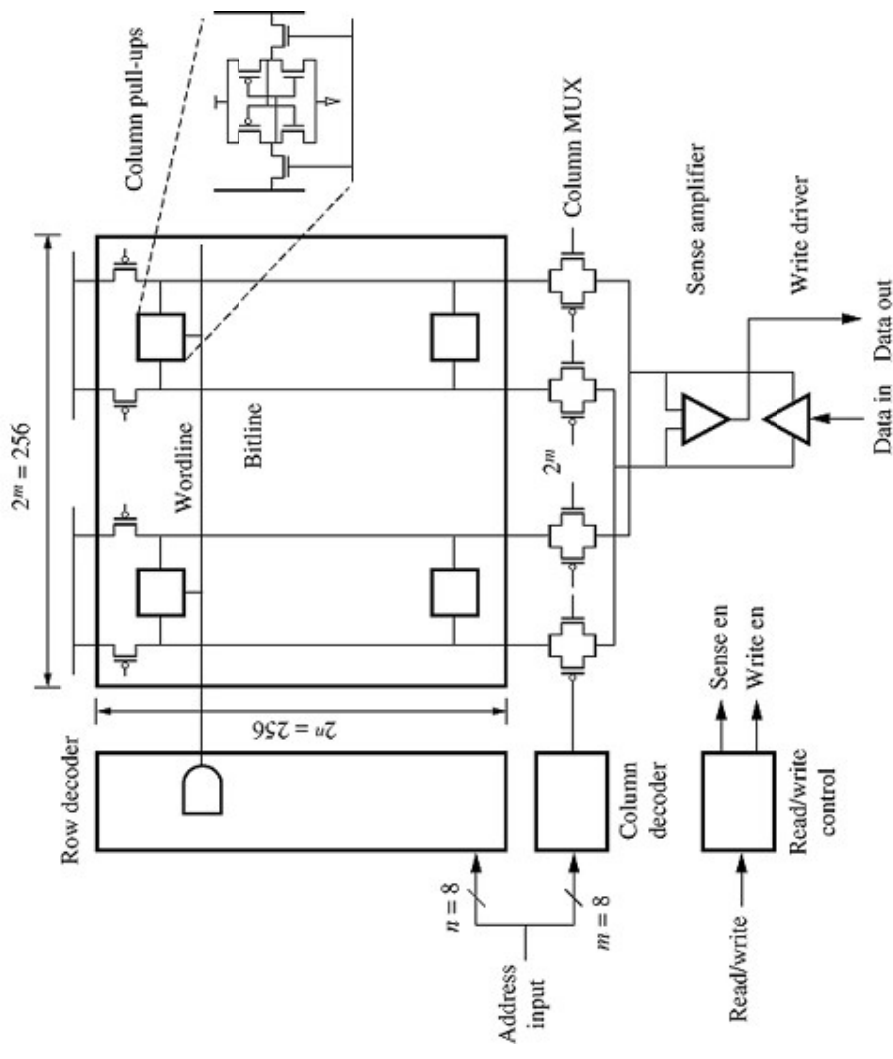
Memory organization

- Random access
- Wordline, bitline, cell



Architecture of memory design

- N-bit decoder for X and Y
- Peripheral circuits



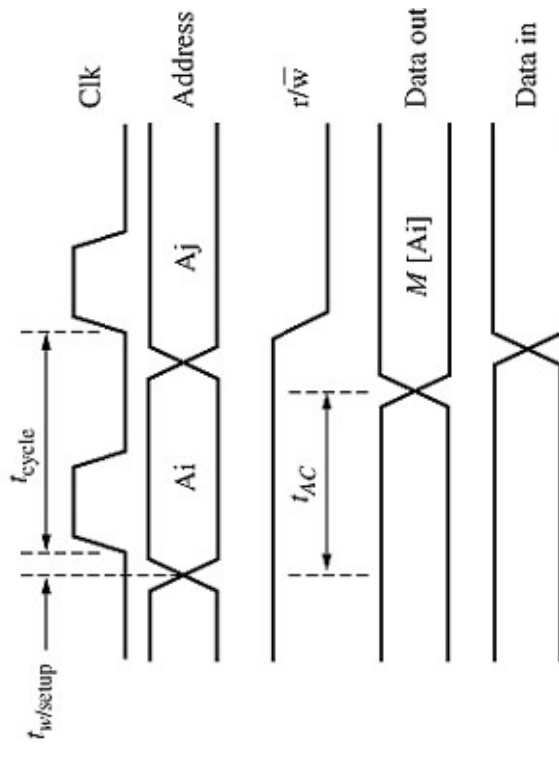
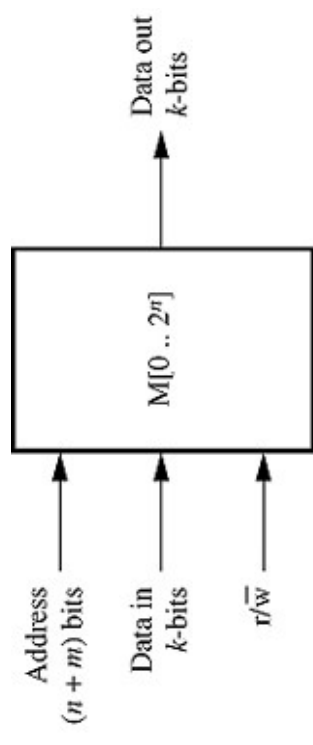
Types of memory



- ❑ Random-access memory (RAM)
- ❑ SRAM and DRAM
- ❑ Read-only memory (ROM), nonvolatile memory
- ❑ Mask-programmed ROM
- ❑ Programmable ROM
- ❑ Erasable programmable ROM
- ❑ Flash memory
- ❑ Ferroelectric RAM (FRAM)

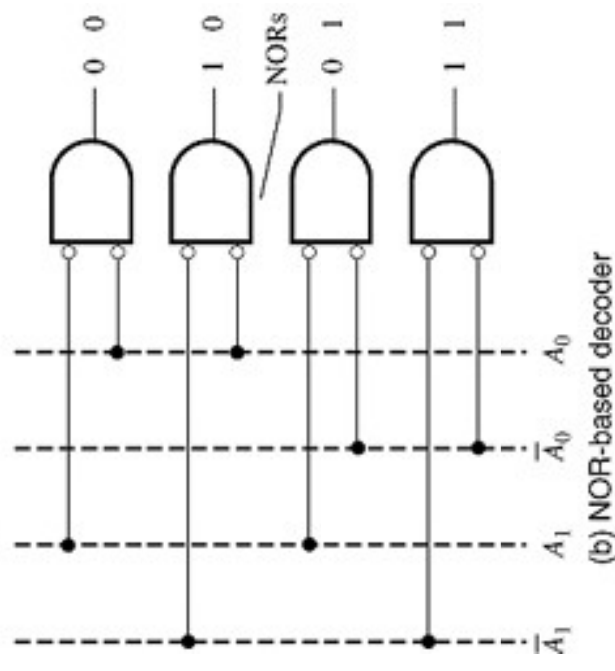
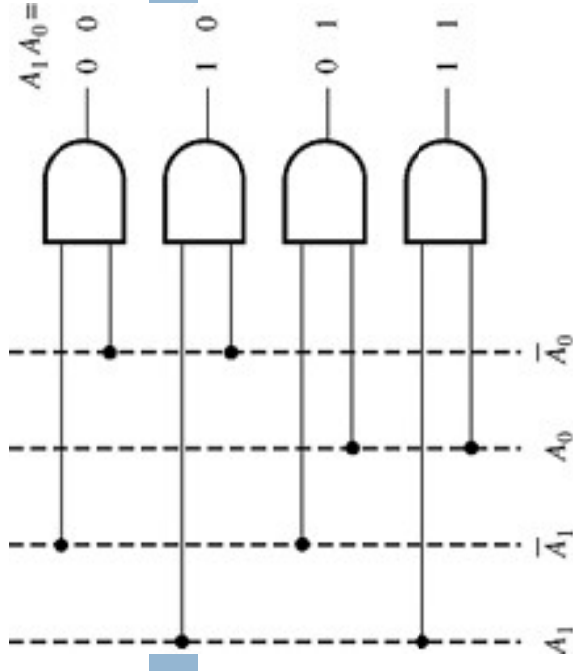
Memory timing

- Read access time (t_{ac})
- Cycle time (t_{cycle})
- Set-up time (t_{set-up})

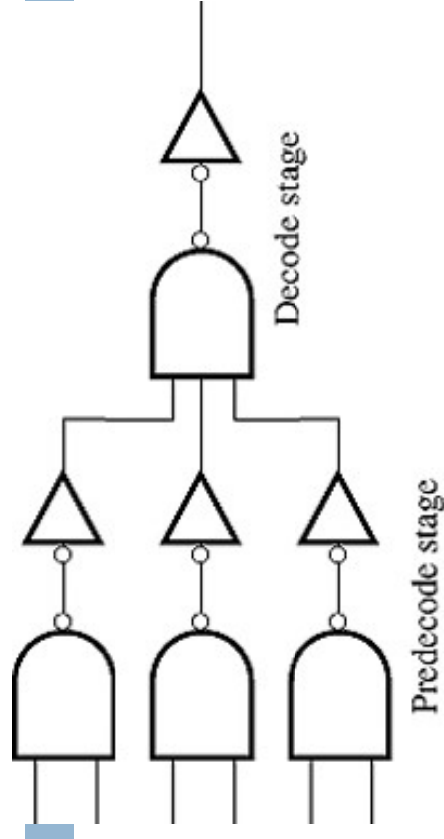


Decoders

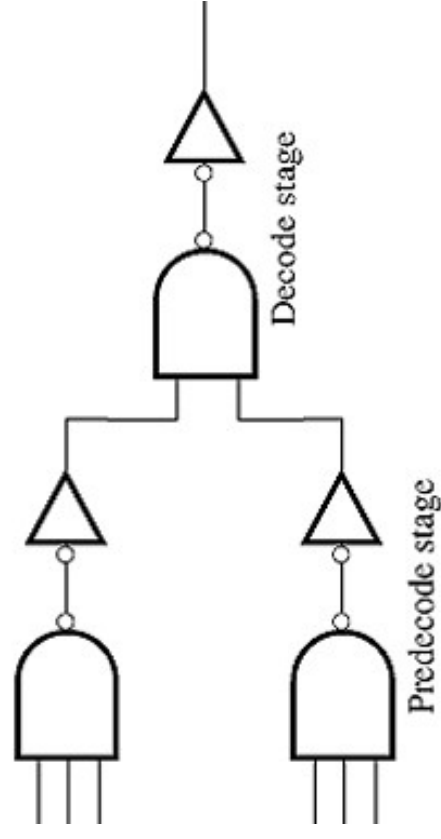
- Nand or nor can be used
- Cascaded gate is more general than n-input gate
- Pre-decoding and main-decoding



Predecoder configurations



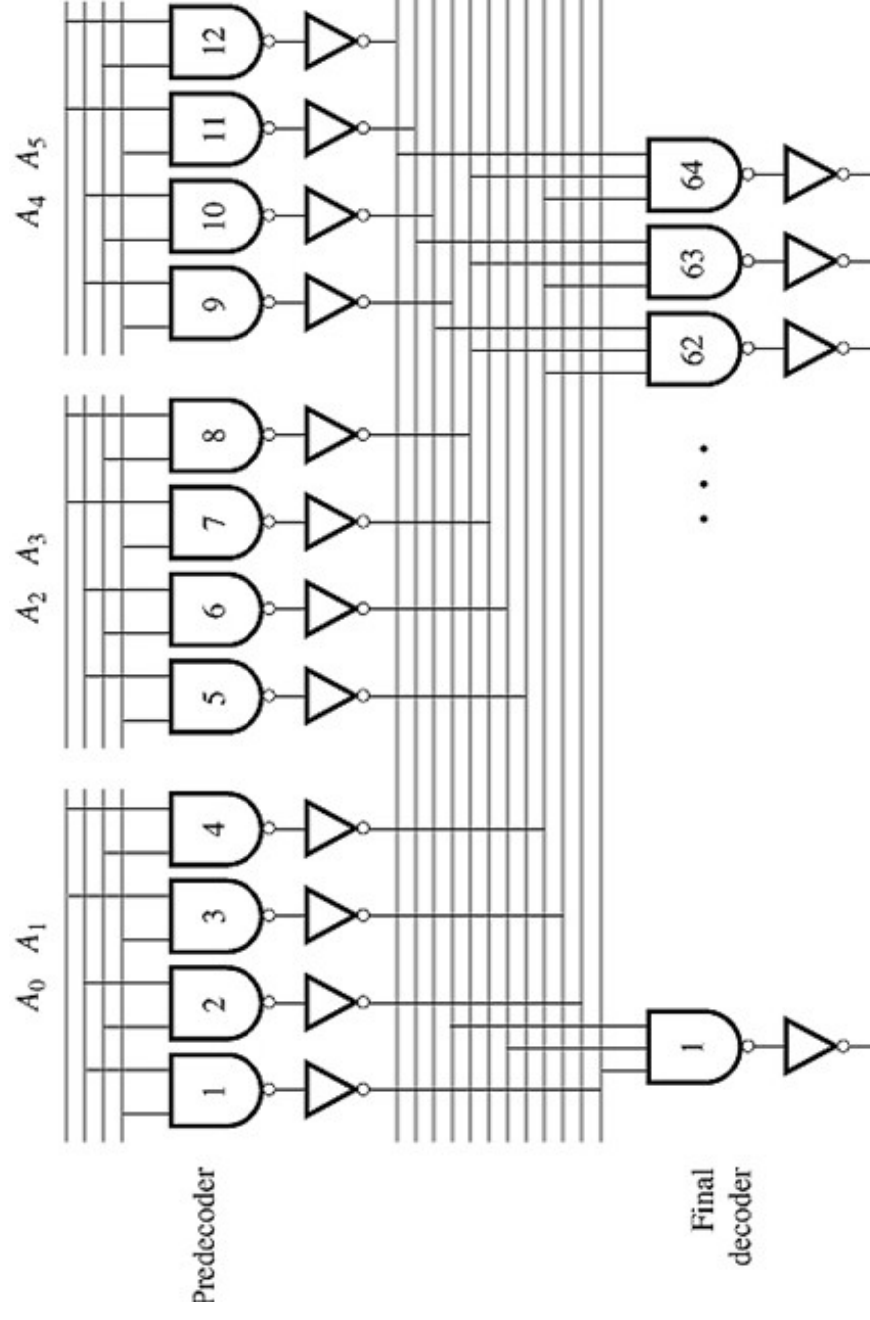
(a)



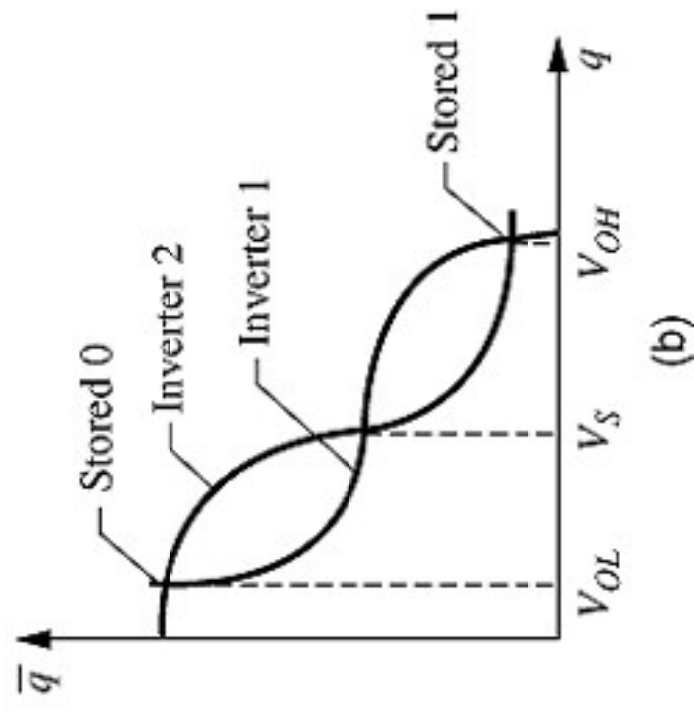
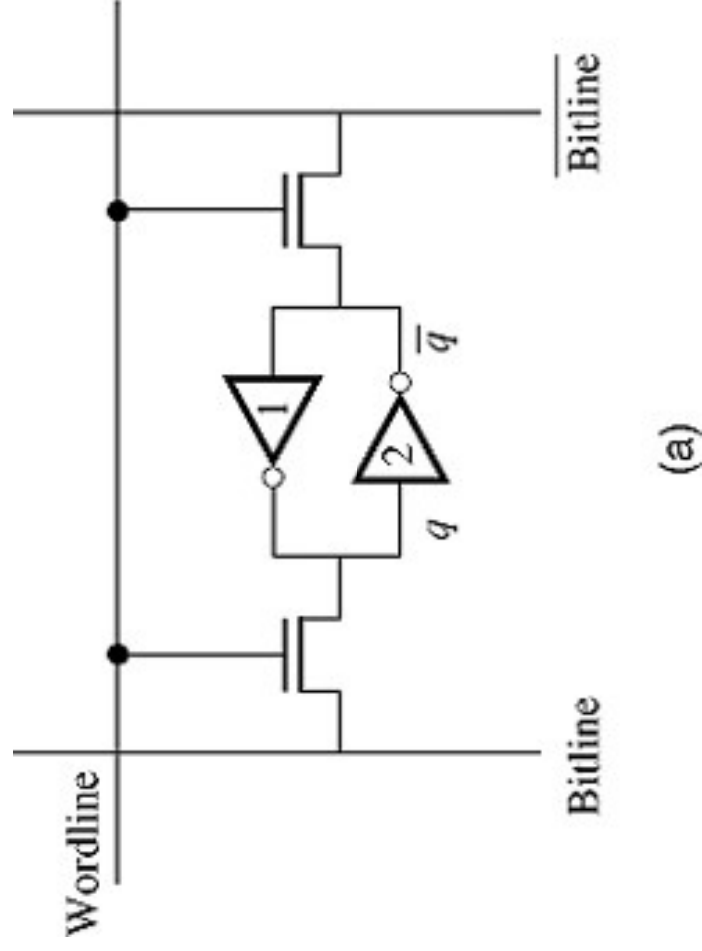
(b)

Structure of two-level decoder

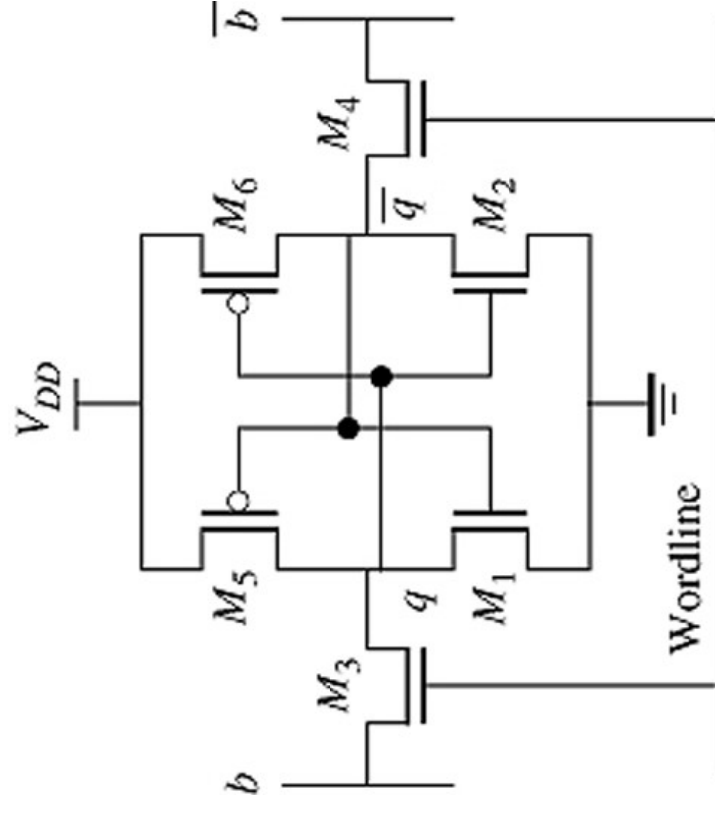
- 6-bit address



Static RAM cell



6 transistor SRAM cell



Wordline and bitline configuration

$C_{word} = (2 * \text{gate cap} + \text{wire cap}) * \# \text{ of cells in row}$

$C_{bit} = (\text{source/drain cap} + \text{wire cap} + \text{contact cap}) * \# \text{ of cells in column}$

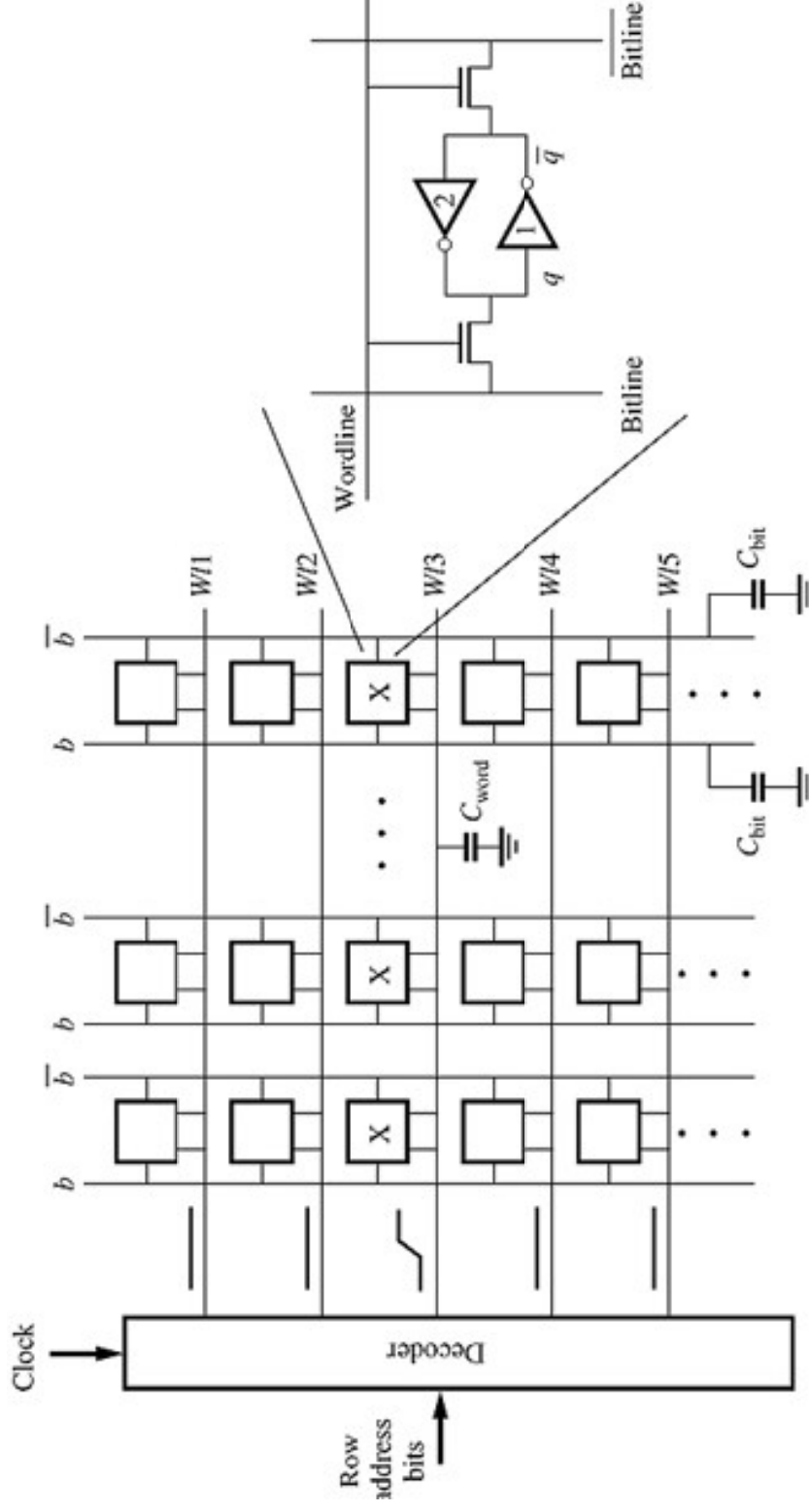
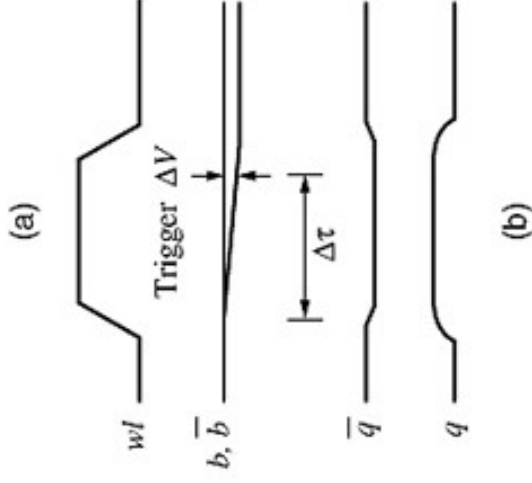


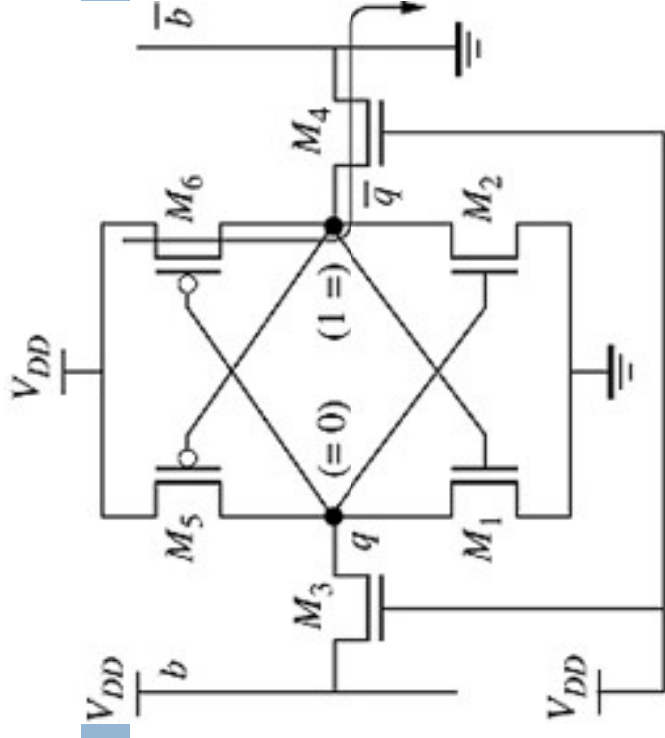
Figure 1(a) is a schematic diagram of a 1T1R1C1 crossbar array. It shows a 2x2 grid of access transistors (M1-M4) and a central storage capacitor (Cbit). The word line (wl) is connected to the gates of M1 and M2. The bit line (bl) is connected to the gates of M3 and M4. The storage capacitor Cbit is connected to the nodes q and q-bar. The array is biased with VDD and ground. Figure 1(b) is a cross-sectional view of the array showing the trigger voltage (Trigger ΔV) and the threshold voltage ($\Delta\tau$) of the access transistors.



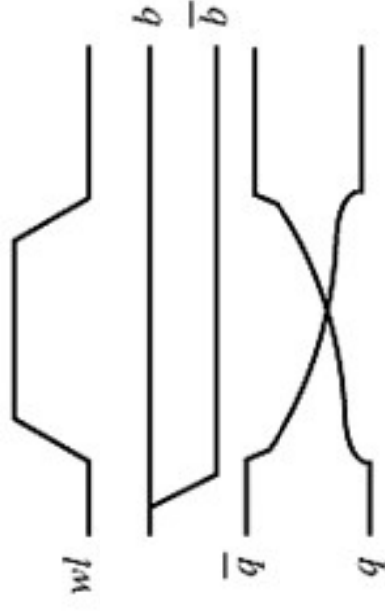
Write operation

$$W4/W6=1.5$$

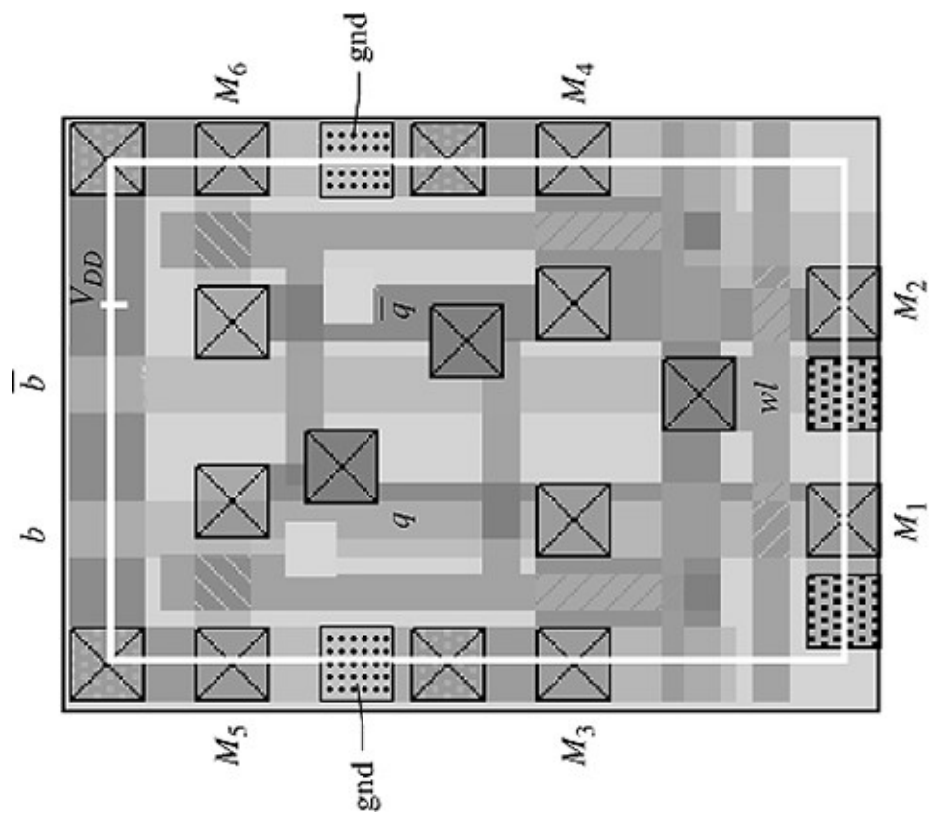
Think of tradeoff between M4 and M6



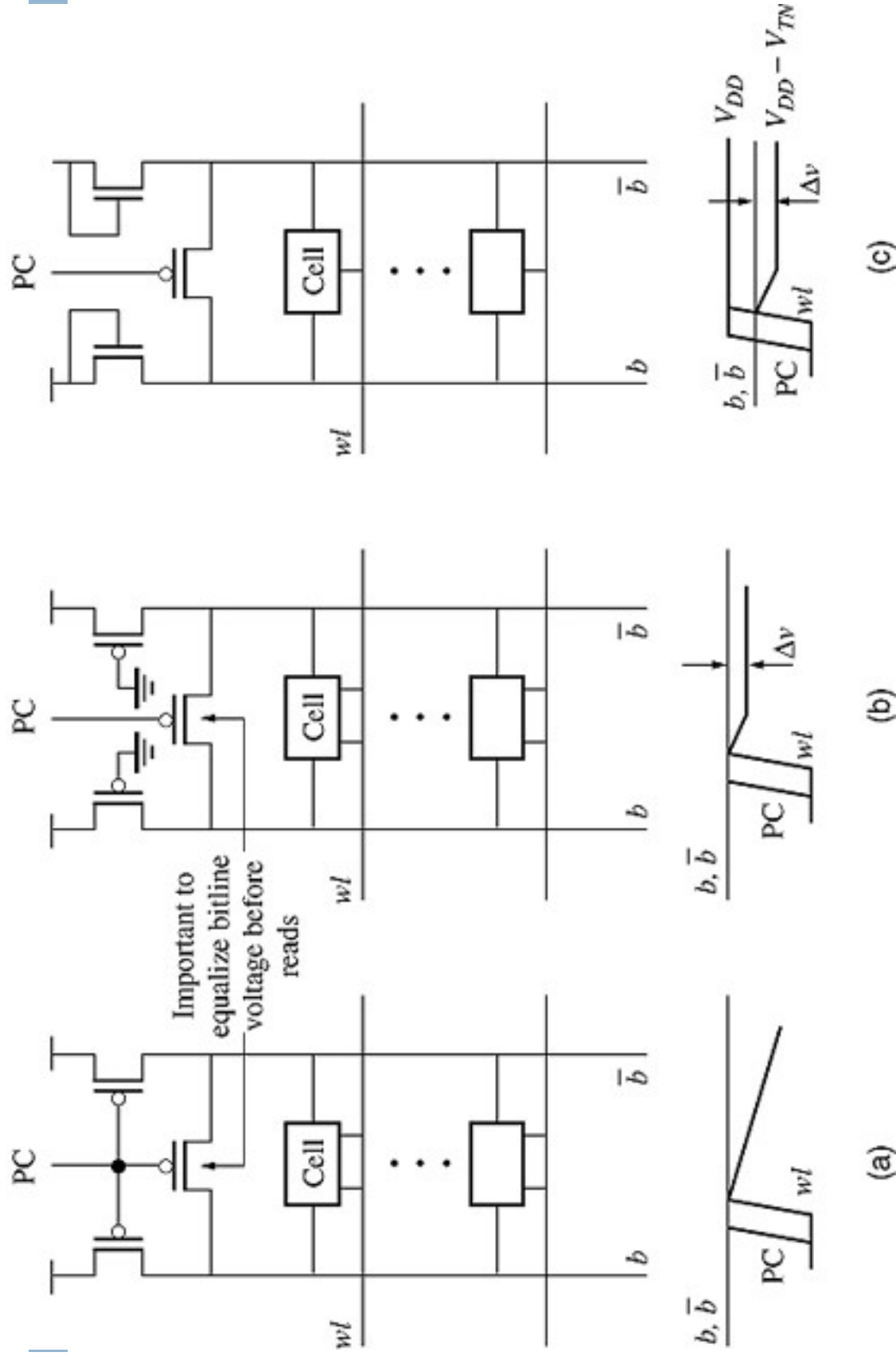
(a)



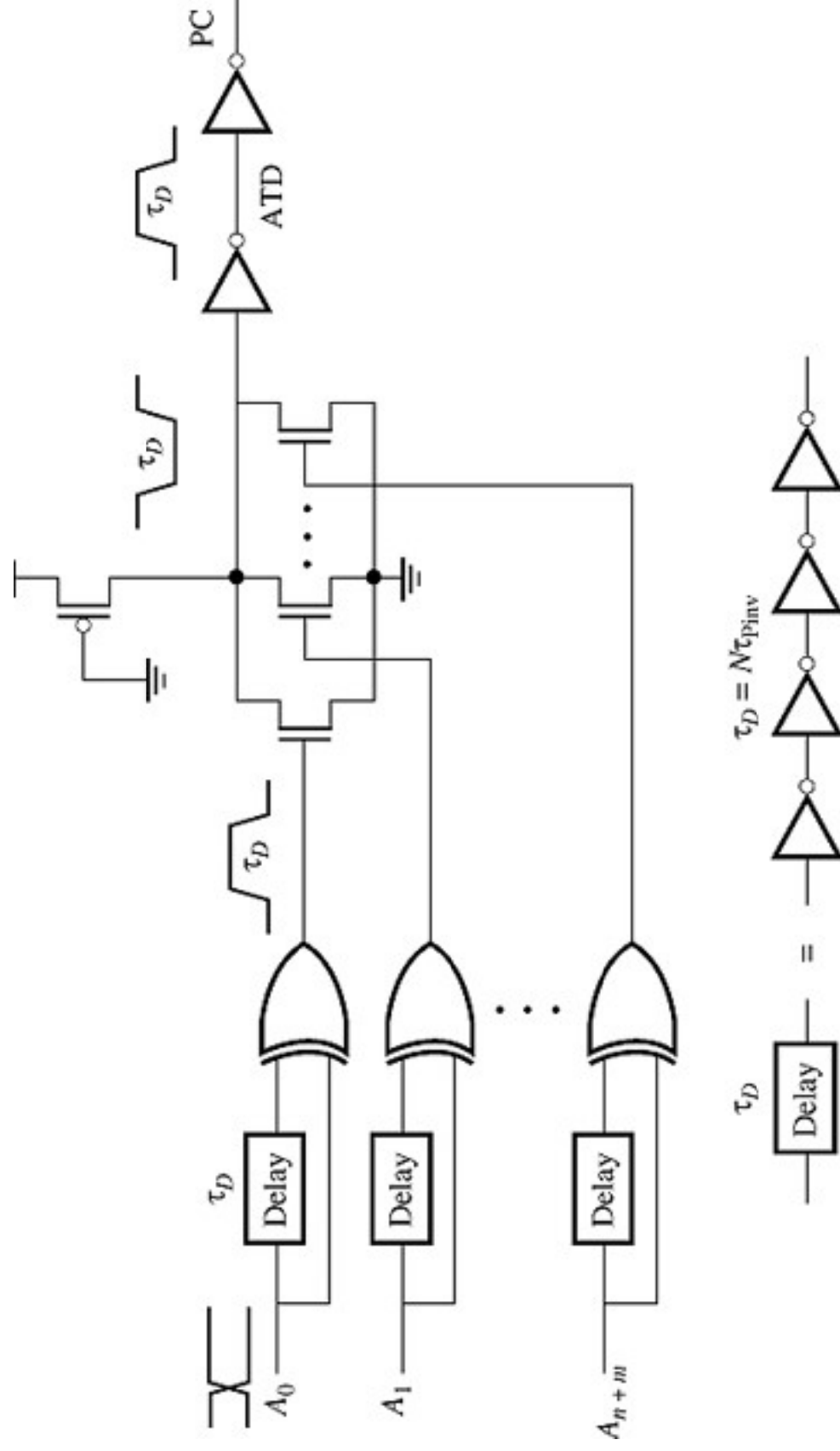
(b)



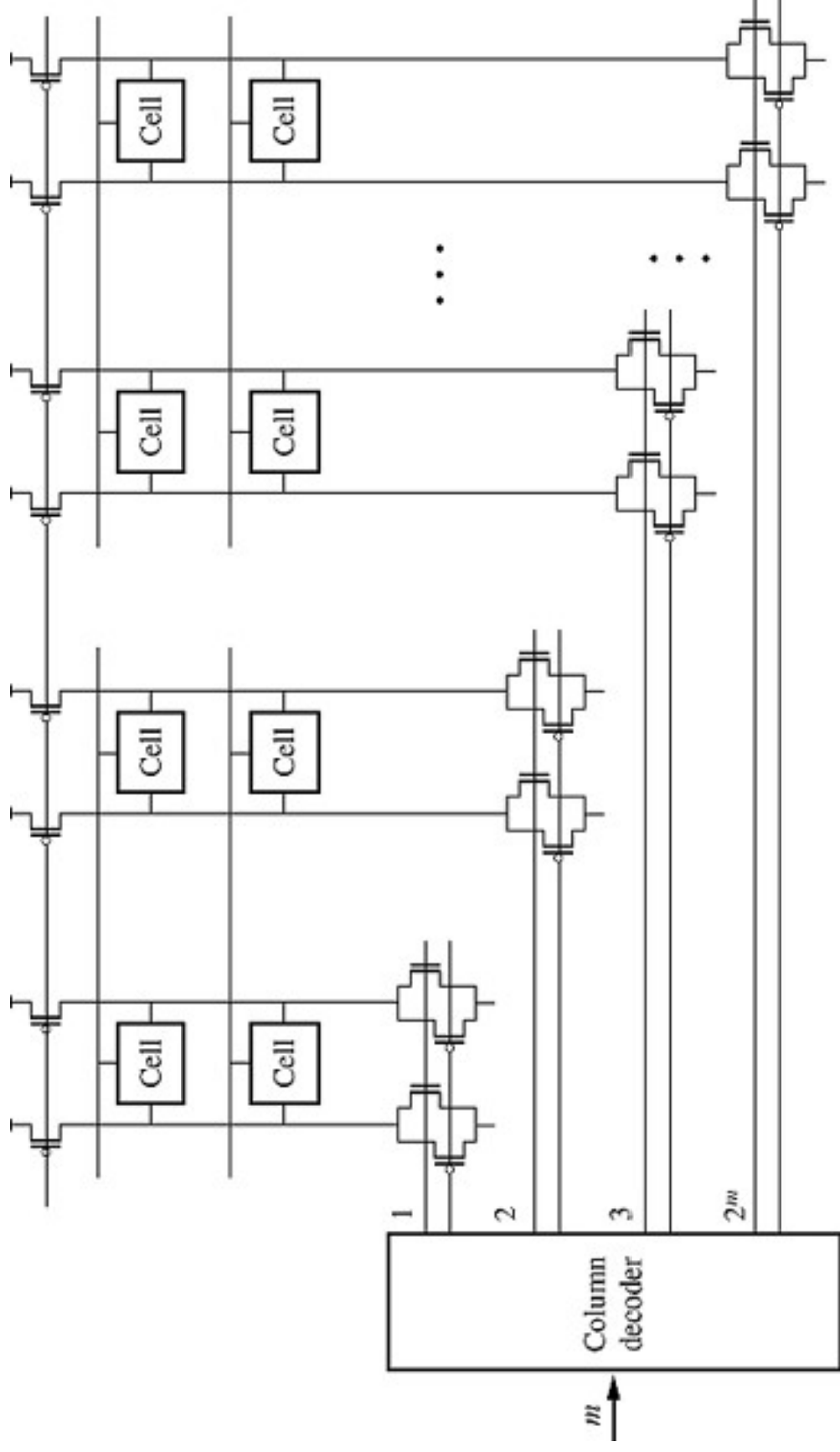
Column pull-up configurations



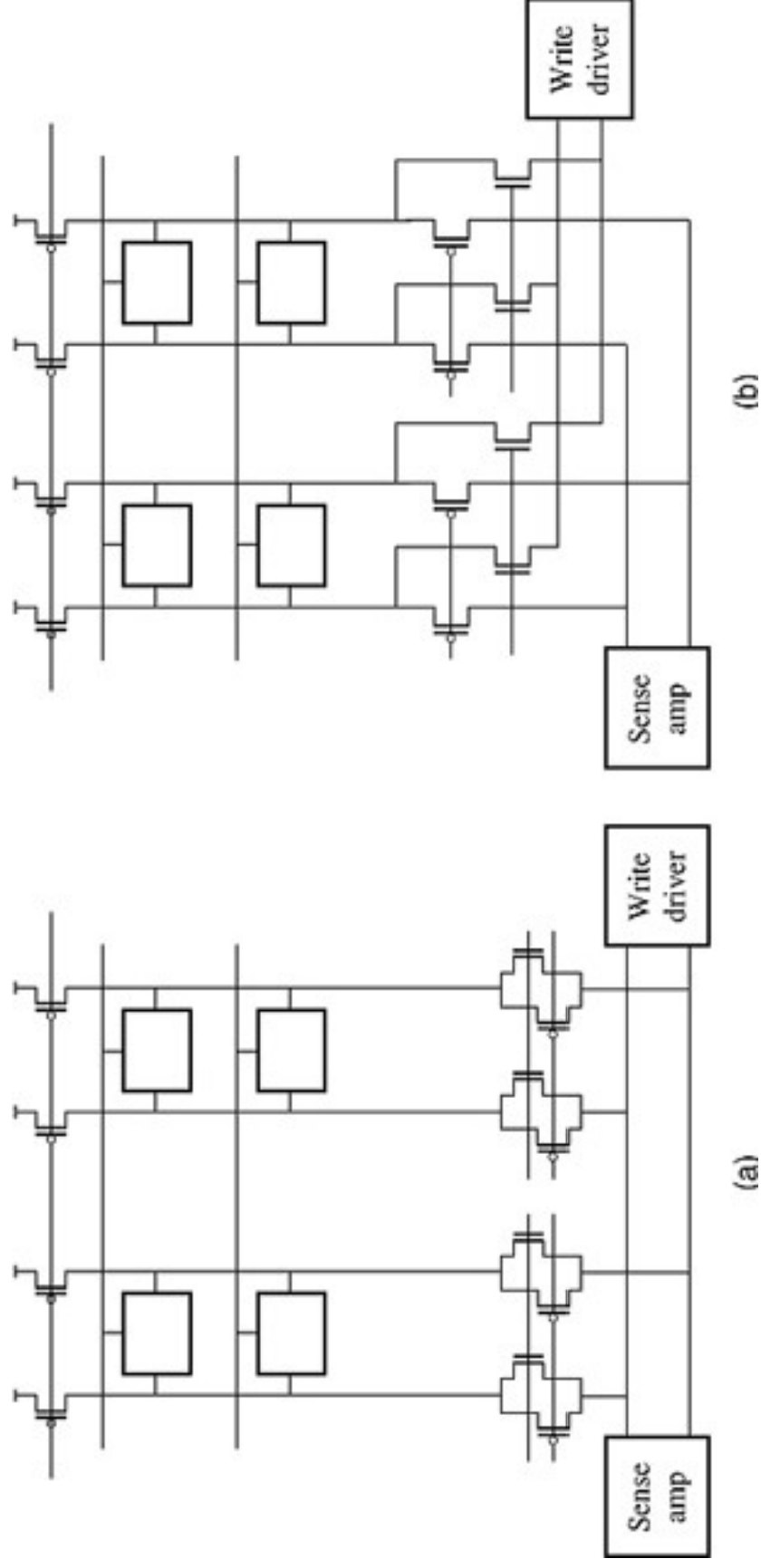
Address transition detection (ATD)



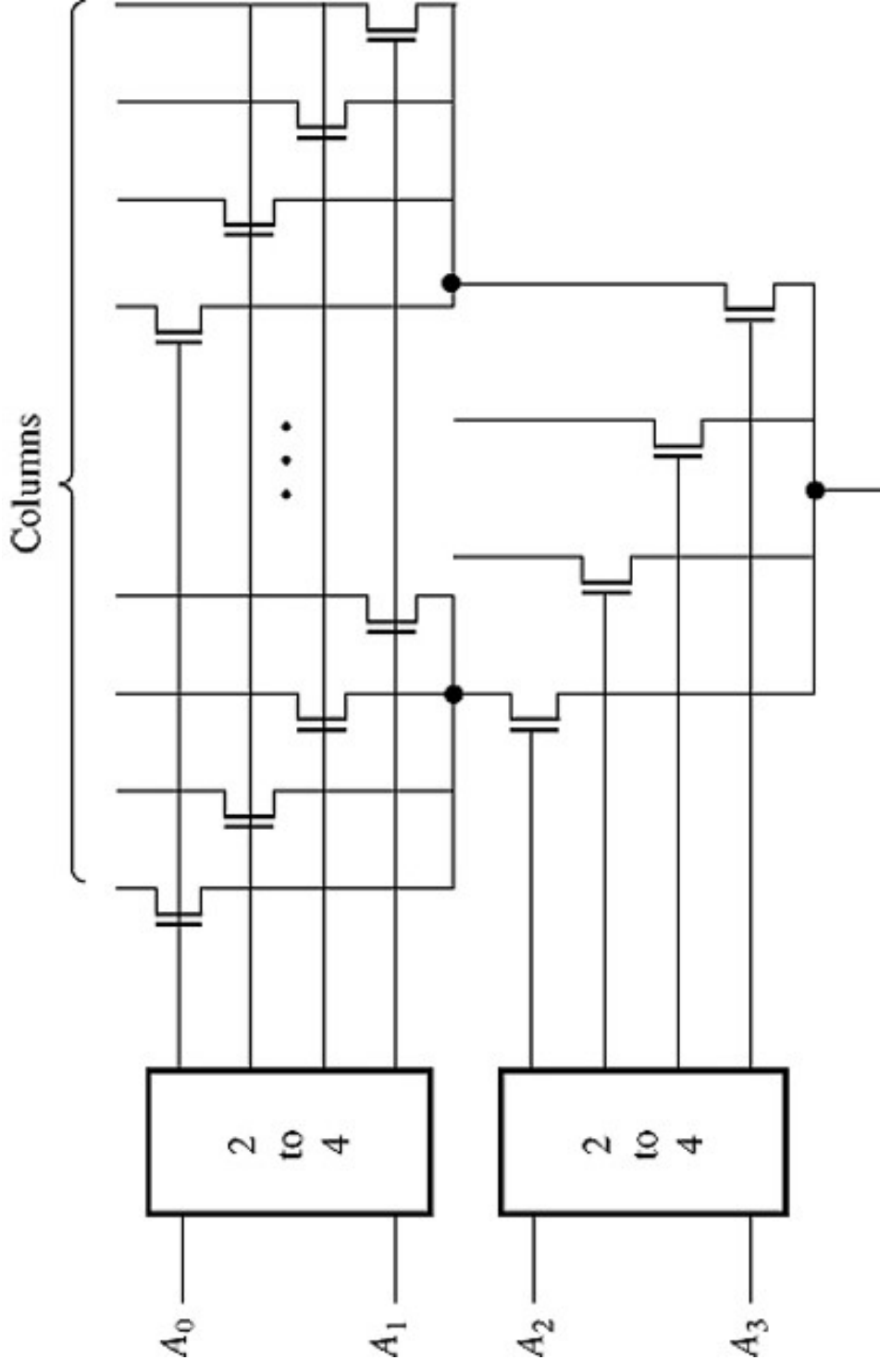
Column decoding and multiplexing



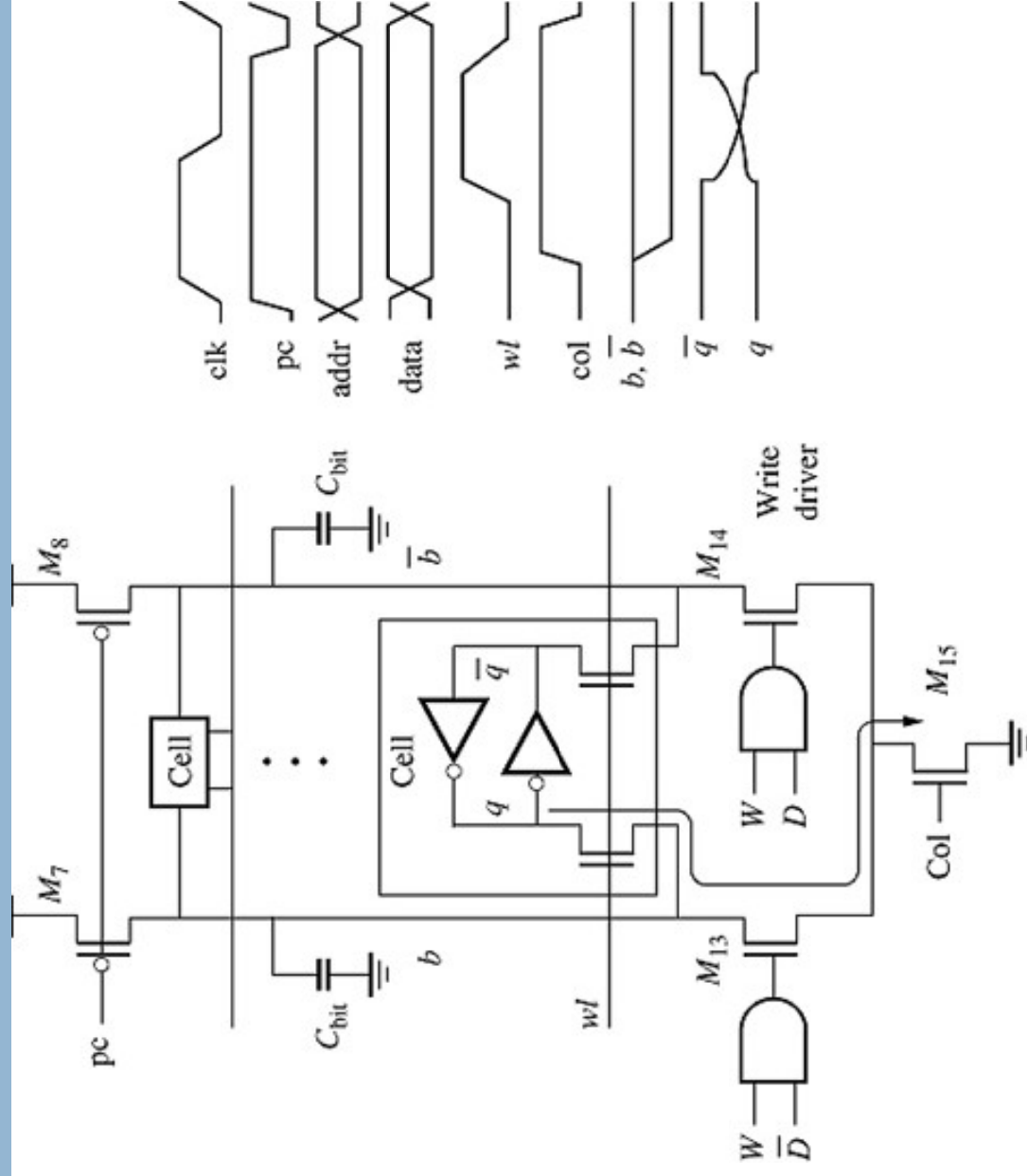
Column selection

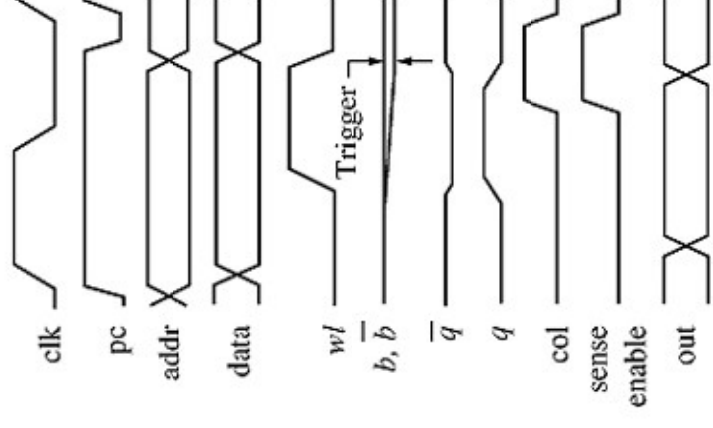


Two-level tree decoder for a 4-bit column address

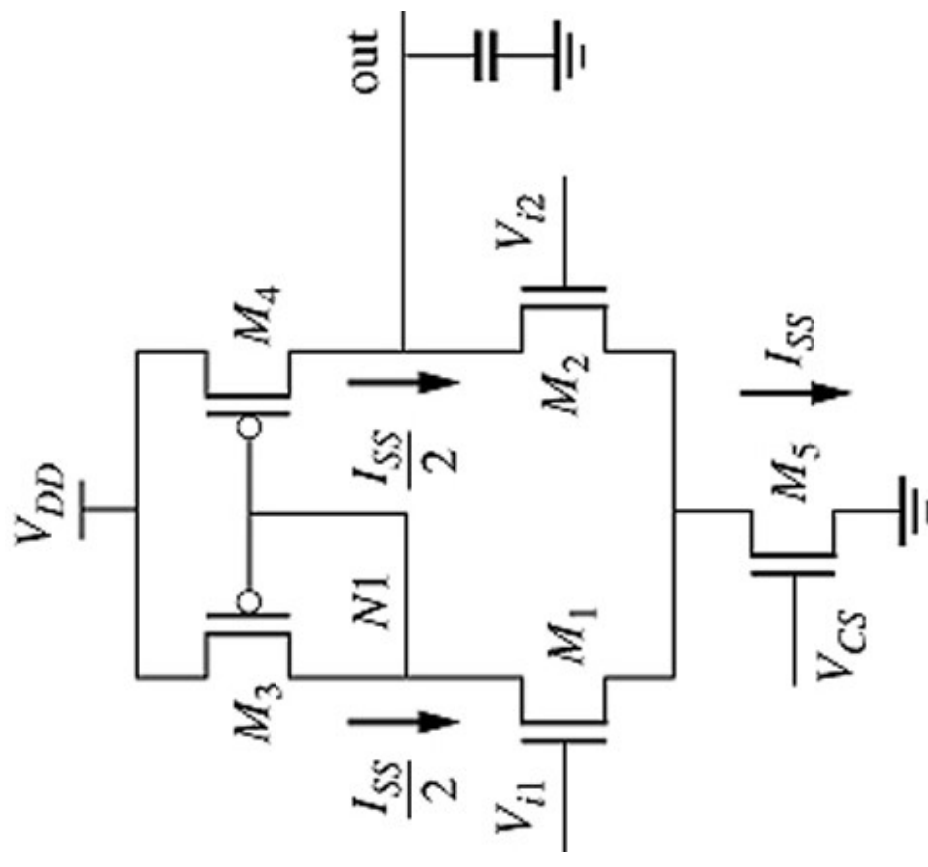


Write circuit

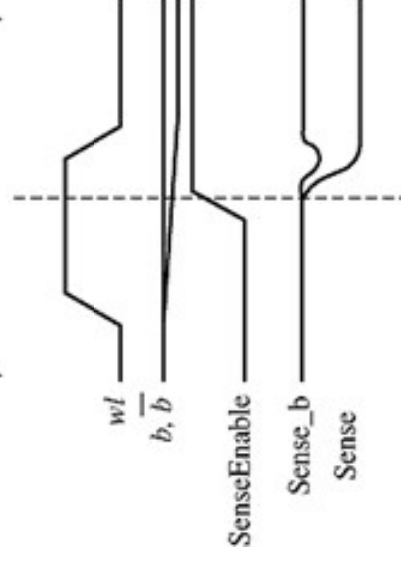
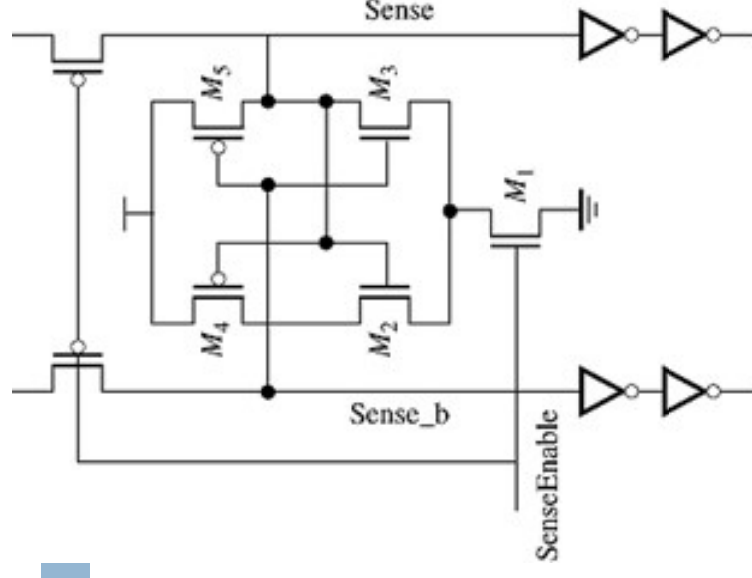




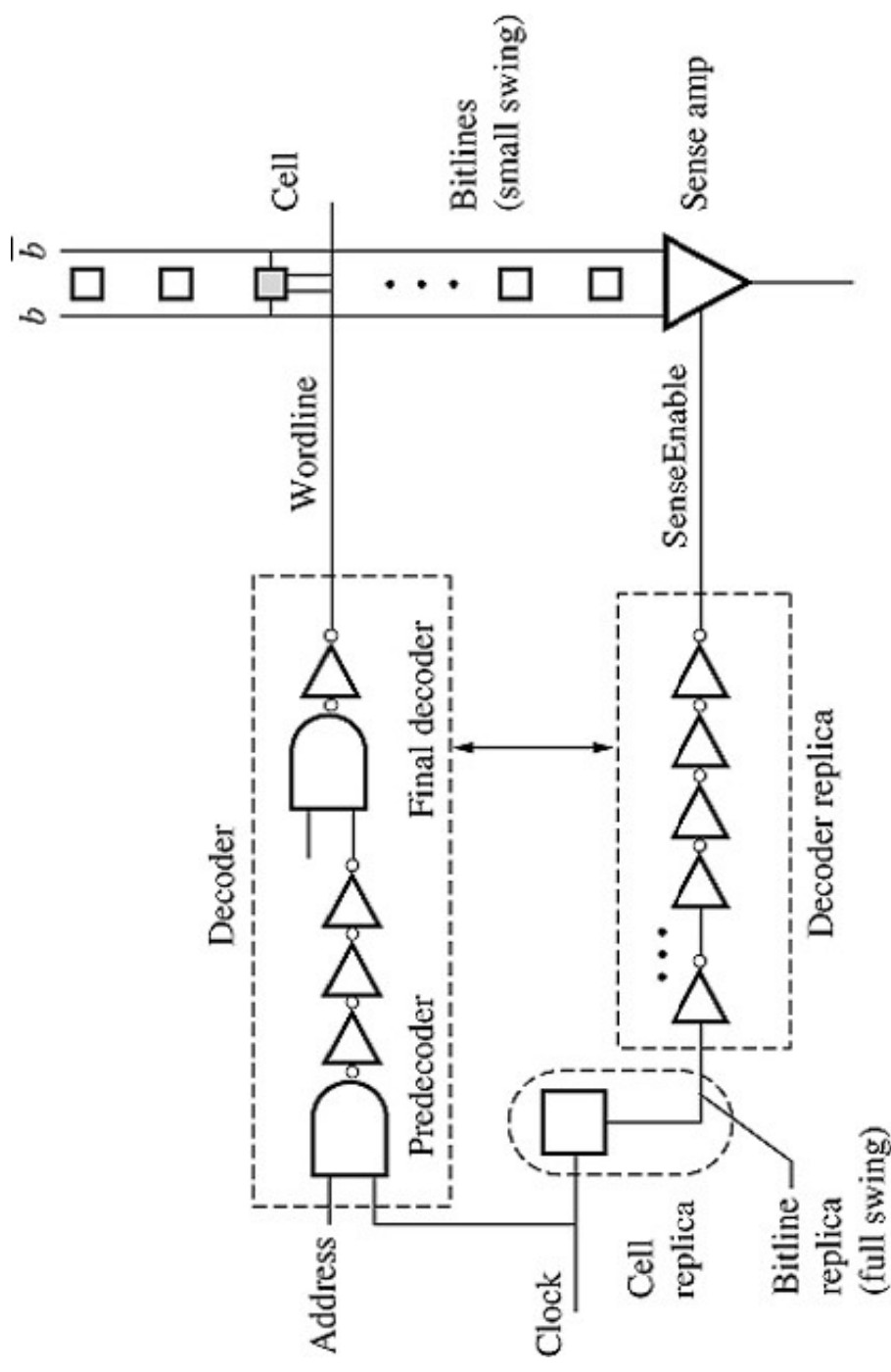
Differential voltage sense amp



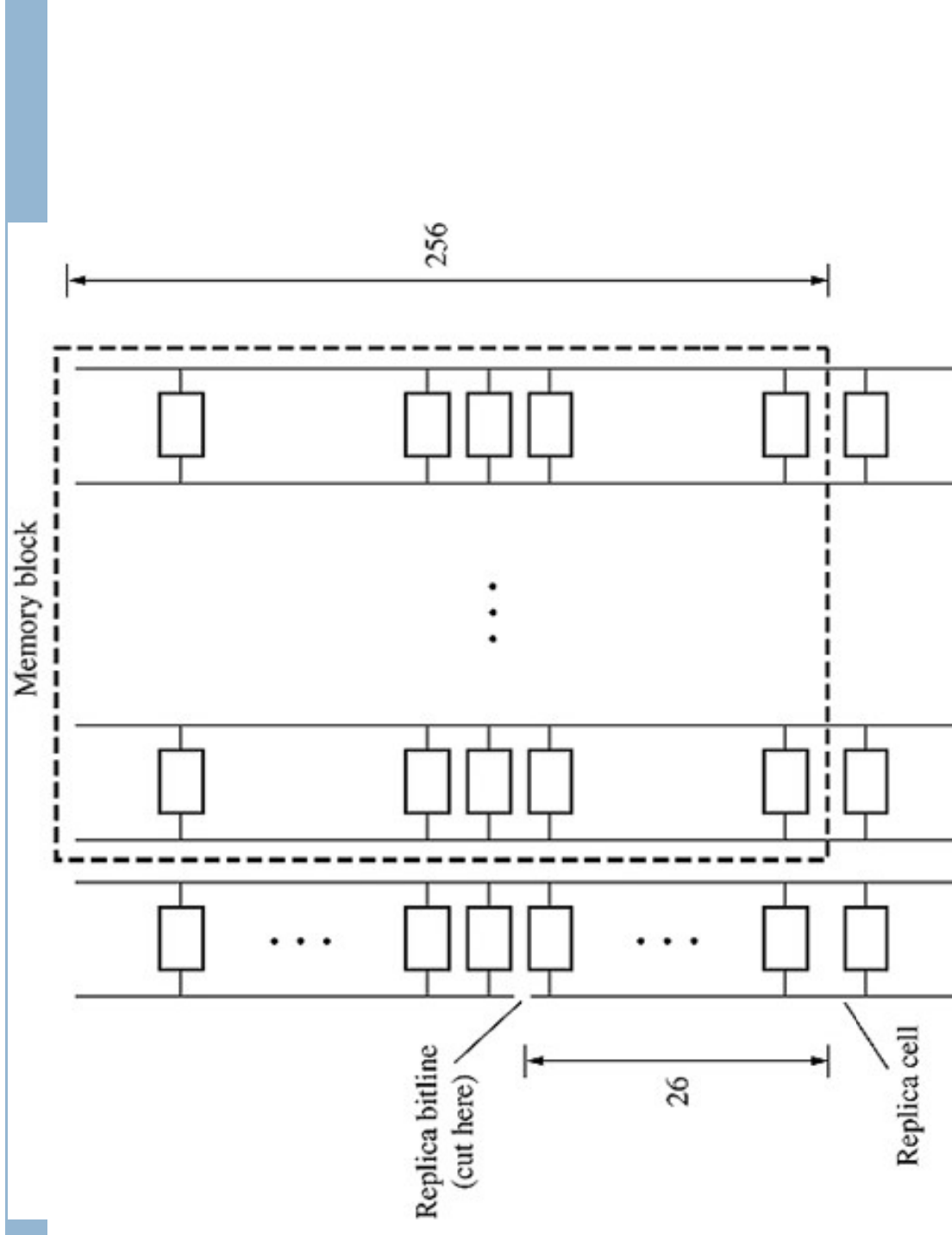
Latch-based sense amplifier



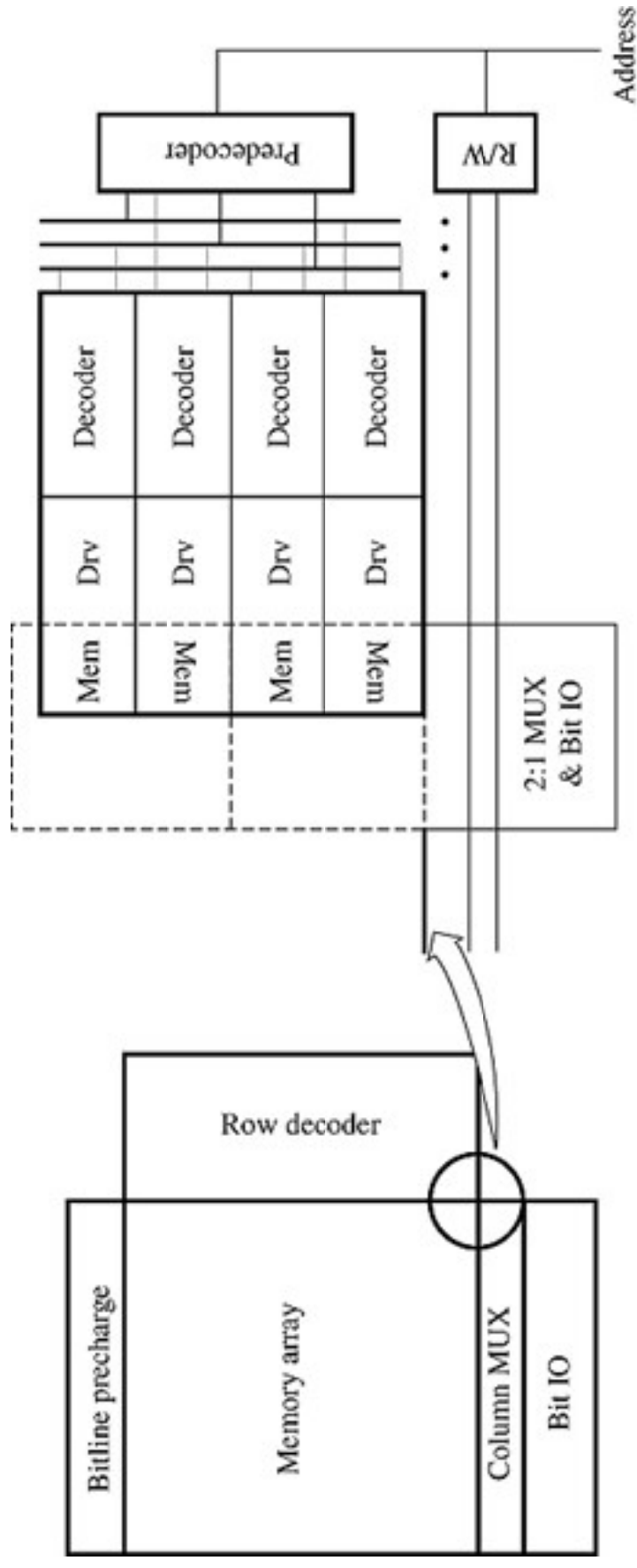
Replica circuit for sense amplifier clock enable

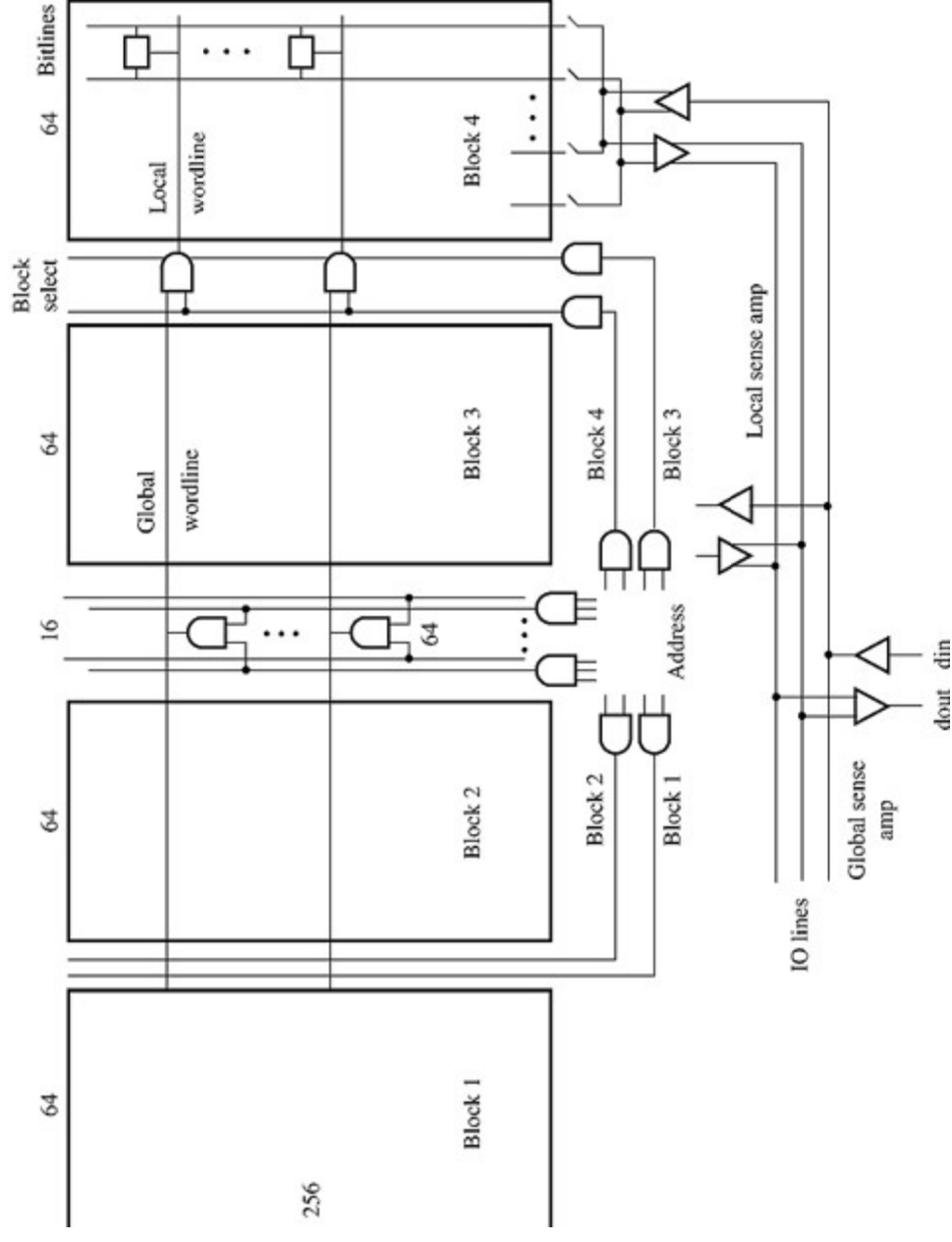


Replica cell design



Memory architecture





Bitline partitioning to reduce delay

